

IN THE SPECIFICATION

Please replace the paragraph at column 1, lines 22-36, with the following rewritten paragraph:

B1
The reference numeral 5 designates a P⁺ base layer; 6 designates an N⁺ emitter layer; 7 designates a gate insulating film made of silicon oxide; 8 designates a gate electrode of polysilicon; 9 designates a gate interconnection line of Al; 10 designates an emitter electrode; 11 designates guard rings; 12 designates a passivation film for isolation between the gate electrode 8 and the emitter electrode 10; 13 designates an emitter wire bonding region; 14 designates a surface protective film of silicon nitride for covering the IGBT surface except the emitter wiring bonding region 13 and a gate bonding pad (not shown) which is a part of the gate interconnection line [8]9; 15 designates a channel stopper; 16 designates a silicon oxide film; 17 designates a polysilicon film; 18 designates a passivation film; and 19 designates a collector electrode.